

Ganesh Balakrishnan

List of Publications by Year in descending order

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198
papers

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147566

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199
docs citations

199
times ranked

2715
citing authors

#	ARTICLE	IF	CITATIONS
1	Photoluminescence and minority carrier lifetime of quinary GaInAsSbBi grown on GaSb by molecular beam epitaxy. Applied Physics Letters, 2022, 120, .	1.5	5
2	Scaling Challenges in High Power Photonic Crystal Surface-Emitting Lasers. IEEE Journal of Quantum Electronics, 2022, 58, 1-9.	1.0	11
3	Imaging of surface acoustic waves on GaAs using 2D confocal Raman microscopy and atomic force microscopy. Applied Physics Letters, 2021, 118, .	1.5	3
4	Submonolayer Quantum-Dot Based Saturable Absorber for Femtosecond Pulse Generation. Journal of Electronic Materials, 2021, 50, 2710-2715.	1.0	2
5	Atomic-scale Structural Imaging of Interfacial Defects in GaAs(001)-based Heterostructures. Microscopy and Microanalysis, 2021, 27, 2356-2357.	0.2	0
6	Controllable finite ultra-narrow quality-factor peak in a perturbed Dirac-cone band structure of a photonic-crystal slab. Applied Physics Letters, 2021, 119, .	1.5	6
7	Mid-infrared interband cascade light emitting devices grown on off-axis silicon substrates. Optics Express, 2021, 29, 35426.	1.7	5
8	Fabrication of Photonic Crystal Surface Emitting Lasers (PCSELs) by Epitaxial Regrowth. , 2021, , .		1
9	Maintaining atomically smooth GaAs surfaces after high-temperature processing for precise interdiffusion analysis and materials engineering. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2021, 39, .	0.6	5
10	InGaSb Defect Filter Layer to Improve Performance of GaSb Solar Cells Grown on GaAs Substrates. Journal of Electronic Materials, 2020, 49, 7153-7158.	1.0	3
11	Comparison of carrier localization effects between InAs quantum dashes and quantum dots in a DWELL (dashes- or dots-in-a-well) configuration. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 124, 114376.	1.3	1
12	A transmission electron microscopy study of dislocation propagation and filtering in highly mismatched GaSb/GaAs heteroepitaxy. Journal of Applied Physics, 2020, 128, 225301.	1.1	2
13	Vertical carrier transport in strain-balanced InAs/InAsSb type-II superlattice material. Applied Physics Letters, 2020, 116, .	1.5	27
14	Influence of quantum dot morphology on the optical properties of GaSb/GaAs multilayers. Applied Physics Letters, 2020, 116, .	1.5	5
15	Epitaxial Regrowth and Hole Shape Engineering for Photonic Crystal Surface Emitting Lasers (PCSELs). Journal of Crystal Growth, 2020, 535, 125531.	0.7	12
16	Revealing Temperature-Dependent Absorption and Emission Enhancement Factors in Plasmon Coupled Semiconductor Heterostructures. ACS Applied Electronic Materials, 2019, 1, 1439-1448.	2.0	4
17	InAs FinFETs Performance Enhancement by Superacid Surface Treatment. IEEE Transactions on Electron Devices, 2019, 66, 1856-1861.	1.6	10
18	Temperature-Dependent Minority-Carrier Mobility in $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ Type-II Heterostructures. Applied Physics Letters, 2019, 115, 121101.	1.5	13

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19	Optically Pumped 1.5 μ m Low Threshold Photonic Crystal Surface Emitting Lasers Grown on GaAs Substrate. , 2019, , .		2
20	Carrier concentration and transport in Be-doped InAsSb for infrared sensing applications. Infrared Physics and Technology, 2019, 96, 184-191.	1.3	5
21	Tailoring Second Harmonic Diffraction in GaAs Metasurfaces via Crystal Orientation. , 2019, , .		1
22	Enhanced Optical Nonlinearities in All-Dielectric Metasurfaces. , 2019, , .		1
23	Wide-temperature-range characterization of 1.55- μ m phosphorus-free multiple-quantum-well lasers grown by MBE on InP. , 2019, , .		0
24	Temperature dependent absorption and emission enhancement factors in plasmon coupled semiconductor heterostructures. , 2019, , .		1
25	Interplay between total thickness and period thickness in the phonon thermal conductivity of superlattices from the nanoscale to the microscale: Coherent versus incoherent phonon transport. Physical Review B, 2018, 97, .	1.1	48
26	Temperature dependence of GaSb and AlGaSb solar cells. Current Applied Physics, 2018, 18, 752-761.	1.1	20
27	High-Speed InP-Based p-i-n Photodiodes With InGaAs/GaAsSb Type-II Quantum Wells. IEEE Photonics Technology Letters, 2018, 30, 399-402.	1.3	11
28	Multiple Metamaterial Pattern Integration for Polarization Selective Photodetector Applications. MRS Advances, 2018, 3, 1907-1912.	0.5	0
29	Going solo: Hierarchical task analysis of the second driver in "two-up" (multi-person) freight rail operations. Applied Ergonomics, 2018, 70, 202-231.	1.7	16
30	Epitaxial lift-off of high quality pixelated thin-film GaSb solar cells. , 2018, , .		0
31	Growth temperature optimization of interfacial misfit technique for growth of GaSb subcells on GaAs substrates. , 2018, , .		0
32	Experimental Evidence of Suppression of Subterahertz Phonons and Thermal Conductivity in GaAs/AlAs Superlattices Due to Extrinsic Scattering Processes. Journal of Physical Chemistry C, 2018, 122, 29577-29585.	1.5	5
33	Pixelated GaSb solar cells on silicon by membrane bonding. Applied Physics Letters, 2018, 113, 123502.	1.5	3
34	Modeling and experimental realization of modelocked VECSEL producing high power sub-100 fs pulses. Applied Physics Letters, 2018, 113, .	1.5	23
35	Light-Emitting Metasurfaces: Simultaneous Control of Spontaneous Emission and Far-Field Radiation. Nano Letters, 2018, 18, 6906-6914.	4.5	126
36	InP-Based Waveguide-Integrated Photodiodes With InGaAs/GaAsSb Type-II Quantum Wells and 10-GHz Bandwidth at 2 μ m Wavelength. Journal of Lightwave Technology, 2018, 36, 4981-4987.	2.7	14

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37	Reducing threading dislocation density in GaSb photovoltaic devices on GaAs by using AlSb dislocation filtering layers. Solar Energy Materials and Solar Cells, 2018, 185, 21-27.	3.0	13
38	Degradation mechanism of SESAMs under intense ultrashort pulses in modelocked VECSELS. , 2018, , .		2
39	Structure and cavity geometry optimization for ultrashort and high power pulse generation from a VECSEL. , 2018, , .		0
40	Multi-Angle VECSEL Cavities for Dispersion Control and Peak-Power Scaling. IEEE Photonics Technology Letters, 2017, 29, 326-329.	1.3	13
41	Multi-angle VECSEL cavities for dispersion control and multi-color operation. Proceedings of SPIE, 2017, , .	0.8	0
42	Active Mediation of Plasmon Enhanced Localized Exciton Generation, Carrier Diffusion and Enhanced Photon Emission. Scientific Reports, 2017, 7, 864.	1.6	7
43	Reduction of reverse leakage current in selective area grown GaN based core shell nanostructure LEDs using AlGaIn layers. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600776.	0.8	14
44	AlGaSb-Based Solar Cells Grown on GaAs: Structural Investigation and Device Performance. IEEE Journal of Photovoltaics, 2017, 7, 1795-1801.	1.5	8
45	Recent advances in high power microwave sources and the science of electronics in extreme electromagnetic environments at the university of new mexico. , 2017, , .		1
46	Thermal plasmons controlled by different thermal-convolution paths in tunable extrinsic Dirac structures. Physical Review B, 2017, 96, .	1.1	24
47	Top-down fabrication for III-nitride nanophotonics. , 2017, , .		0
48	InP-based multiple type-II quantum-well integrated waveguide p-i-n photodiodes for mid-infrared detection. , 2017, , .		1
49	Improvement of open-circuit voltage in metamorphic GaSb cells grown on GaAs substrates by using an interfacial misfit array and an AlSb blocking layer. , 2017, , .		0
50	Temperature and distance dependence of plasmon enhanced InAs/InGaAs/GaAs dot-in-a-well near IR emission. , 2017, , .		0
51	High-speed type-II InGaAs/GaAsSb multiple quantum-well integrated waveguide photodiodes at 2 μ m wavelength. , 2017, , .		0
52	Distance and temperature dependent plasmon-enhanced carrier generation and diffusion in InAs/InGaAs/GaAs near-infrared photodetectors. , 2017, , .		0
53	Emission wavelength control in InAs(Sb) quantum dashes-in-a-well structures. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 02L103.	0.6	0
54	Accurate Cloning of the Memory Access Behavior. IPSJ Transactions on System LSI Design Methodology, 2016, 9, 49-60.	0.5	2

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55	AlGaSb based solar cells grown on GaAs by Molecular Beam Epitaxy. , 2016, , .		0
56	Development of thin film metamorphic GaSb cells by epitaxial lift-off from GaAs substrates. , 2016, , .		4
57	Ultrafast characterization of semiconductor gain and absorber devices for mode-locked VECSELs. , 2016, , .		0
58	Investigation of Surface Defects in AlInSb Metamorphic Buffer (MB) Grown on GaSb. Journal of Electronic Materials, 2016, 45, 6258-6264.	1.0	1
59	III-Nitride nanowires lasers. , 2016, , .		0
60	Semipolar InGaN/GaN nanostructure light-emitting diodes on c-plane sapphire. Applied Physics Express, 2016, 9, 032101.	1.1	17
61	Development of III-Sb metamorphic DBR membranes on InP for vertical cavity laser applications. Journal of Crystal Growth, 2016, 439, 104-109.	0.7	0
62	High-Resistivity Semi-insulating AlSb on GaAs Substrates Grown by Molecular Beam Epitaxy. Journal of Electronic Materials, 2016, 45, 2025-2030.	1.0	7
63	Molecular beam epitaxy of high-resistivity AlSb for room-temperature radiation detectors. , 2015, , .		0
64	Characterization of carrier transport properties in strained crystalline Si wall-like structures in the quasi-quantum regime. Journal of Applied Physics, 2015, 118, 134301.	1.1	3
65	MEMST. , 2015, , .		5
66	Time-resolved photo and radio-luminescence studies demonstrate the possibility of using InGaN/GaN quantum wells as fast scintillators. Nanotechnology, 2015, 26, 090501.	1.3	2
67	3 Åm thick GaSb membrane diodes integrated with CVD diamond heat spreaders for thermally managed TPV cells. , 2015, , .		2
68	MeToo: Stochastic Modeling of Memory Traffic Timing Behavior. , 2015, , .		7
69	Ordered arrays of bottom-up III-nitride core-shell nanostructures. , 2015, , .		6
70	Green synthesis of zinc oxysulfide quantum dots using aegle marmelos fruit extract and their cytotoxicity in HeLa cells. RSC Advances, 2015, 5, 16815-16820.	1.7	18
71	Controlled Growth of Ordered III-Nitride Core-Shell Nanostructure Arrays for Visible Optoelectronic Devices. Journal of Electronic Materials, 2015, 44, 1255-1262.	1.0	25
72	Isolating GaSb Membranes Grown Metamorphically on GaAs Substrates Using Highly Selective Substrate Removal Etch Processes. Journal of Electronic Materials, 2015, 44, 1327-1331.	1.0	4

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73	Wavelength beam combining of VECSELs using multiplexed volume Bragg gratings in a compound cavity. Electronics Letters, 2015, 51, 508-510.	0.5	7
74	Thin-Film Gallium Antimonide for Room-Temperature Radiation Detection. Journal of Electronic Materials, 2015, 44, 3288-3293.	1.0	3
75	GaSb thermophotovoltaics: current challenges and solutions. Proceedings of SPIE, 2015, , .	0.8	3
76	Characterization of surface defects on Be-implanted GaSb. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 04E109.	0.6	6
77	Flash extreme ultraviolet holographic microscopy in a table top setup. Proceedings of SPIE, 2014, , .	0.8	0
78	Polarization control in GaN nanowire lasers. Optics Express, 2014, 22, 19198.	1.7	14
79	Recording oscillations of sub-micron size cantilevers by extreme ultraviolet Fourier transform holography. Optics Express, 2014, 22, 4161.	1.7	13
80	Toward dynamic metamaterials for monolithically integrated multilayer polarization filters. , 2014, , .		0
81	Beryllium implant activation and damage recovery study in n-type GaSb. , 2014, , .		3
82	GaSb Thermophotovoltaic Cells Grown on GaAs Substrate Using the Interfacial Misfit Array Method. Journal of Electronic Materials, 2014, 43, 902-908.	1.0	22
83	High Mobility n and p Channels on Gallium Arsenide and Silicon Substrates Using Interfacial Misfit Dislocation Arrays. , 2014, , .		0
84	Low resistance palladium/molybdenum based ohmic contacts to n-GaSb grown on GaAs. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 04E108.	0.6	3
85	Transmission Electron Microscopy-Based Analysis of Electrically Conductive Surface Defects in Large Area GaSb Homoepitaxial Diodes Grown Using Molecular Beam Epitaxy. Journal of Electronic Materials, 2014, 43, 926-930.	1.0	11
86	Selective-Area Growth of III-Nitride Core-Shell Nanowalls for Light-Emitting and Laser Diodes. , 2014, , .		1
87	Understanding the visual skills and strategies of train drivers in the urban rail environment. Work, 2014, 47, 339-352.	0.6	17
88	Time Resolved Holography Scheme Using a Table Top Soft X-Ray Laser. Springer Proceedings in Physics, 2014, , 165-170.	0.1	1
89	Extreme Ultraviolet Nano-holography Scheme to Study the Dynamic of ILMs in Mechanical Nano-oscillators. IEICE Proceeding Series, 2014, 1, 415-418.	0.0	0
90	Temperature dependent carrier dynamics in telecommunication band InAs quantum dots and dashes grown on InP substrates. Journal of Applied Physics, 2013, 113, .	1.1	37

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91	Epitaxial growth of cerium oxide thin films by pulsed laser deposition. Thin Solid Films, 2013, 546, 467-471.	0.8	19
92	Electrical and microstructure analysis of nickel-based low-resistance ohmic contacts to n-GaSb. APL Materials, 2013, 1, .	2.2	15
93	Growth and Optimization of 2- μ m InGaSb/AlGaSb Quantum-Well-Based VECSELS on GaAs/AlGaAs DBRs. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1700611-1700611.	1.9	4
94	Investigation of InAs quantum dashes for 1.45-2.1 μ m vertical external cavity surface emitting laser active regions. Proceedings of SPIE, 2013, , .	0.8	0
95	TEM based analysis of III-Sb VECSELS on GaAs substrates for improved laser performance.. Proceedings of SPIE, 2013, , .	0.8	3
96	Tabletop single-shot extreme ultraviolet Fourier transform holography of an extended object. Optics Express, 2013, 21, 9959.	1.7	33
97	Polarization Properties of GaN Nanowire Lasers. , 2013, , .		1
98	Three-dimensional GaN templates for molecular beam epitaxy of nonpolar InGaN/GaN coaxial light-emitting diodes. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 03C107.	0.6	8
99	Carrier dynamics and photoluminescence quenching mechanism of strained InGaSb/AlGaSb quantum wells. Journal of Applied Physics, 2013, 113, 053505.	1.1	5
100	Ohmic contacts to n-type GaSb grown on GaAs by the interfacial misfit dislocation technique. Proceedings of SPIE, 2013, , .	0.8	6
101	Isolation and characterization of large-area GaSb membranes grown on GaAs substrates. , 2013, , .		0
102	Effect of antimony nano-scale surface-structures on a GaSb/AlAsSb distributed Bragg reflector. Applied Physics Letters, 2013, 102, 063108.	1.5	0
103	Time resolved extreme ultraviolet Fourier transform holography. , 2013, , .		0
104	Polarization switching in GaN nanowire lasers. Applied Physics Letters, 2013, 103, .	1.5	15
105	Ultra-low resistance NiGeAu and PdGeAu ohmic contacts on N-GaSb grown on GaAs. , 2013, , .		2
106	Spectral and Transient Luminescence Measurements on GaSb/AlGaSb Quantum Wells Grown on GaSb/GaAs Heterojunctions with and without Interfacial Misfit Arrays. Japanese Journal of Applied Physics, 2013, 52, 022101.	0.8	0
107	Study of Al ₂ O ₃ /ZrO ₂ (5 nm/20nm) Nanolaminate Composite. Composites Research, 2013, 26, 60-65.	0.1	5
108	Low homologous temperature (<0.2) sputtering of indium films on silicon. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 060602.	0.6	5

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109	Gold substrate-induced single-mode lasing of GaN nanowires. Applied Physics Letters, 2012, 101, 221114.	1.5	32
110	Single-mode lasing of GaN nanowire-pairs. Applied Physics Letters, 2012, 101, .	1.5	63
111	Relaxation dynamics and residual strain in metamorphic AlSb on GaAs. Applied Physics Letters, 2012, 100, .	1.5	9
112	GaN epitaxy on Cu(110) by metal organic chemical vapor deposition. Applied Physics Letters, 2012, 100, .	1.5	4
113	Intracavity laser cooling using a VECSEL. , 2012, , .		4
114	Influence of non-radiative carrier losses on pulsed and continuous VECSEL performance. , 2012, , .		6
115	Demonstration of a Cognitive Radio Front End Using an Optically Pumped Reconfigurable Antenna System (OPRAS). IEEE Transactions on Antennas and Propagation, 2012, 60, 1075-1083.	3.1	93
116	Intrinsic localized modes in two-dimensional vibrations of crystalline pillars and their application for sensing. Journal of Applied Physics, 2012, 112, .	1.1	7
117	Transmission electron microscopy study of metamorphic III-Sb VECSELs on GaAs/AlGaAs distributed Bragg reflectors. , 2012, , .		0
118	WEST: Cloning data cache behavior using Stochastic Traces. , 2012, , .		25
119	Gallium free type II InAs/InAsxSb1-x superlattice photodetectors. Applied Physics Letters, 2012, 101, 071111.	1.5	40
120	A cognitive radio antenna design based on optically pumped reconfigurable antenna system (OPRAS). , 2011, , .		5
121	High-power 1.25- μ m InAs QD VECSEL based on resonant periodic gain structure. Proceedings of SPIE, 2011, , .	0.8	3
122	Lattice mismatched growth for mid-IR VECSELs. Proceedings of SPIE, 2011, , .	0.8	3
123	Power scaling of cw and pulsed IR and mid-IR OPSLs. , 2011, , .		3
124	Growth Mode and Defect Evaluation of GaSb on GaAs Substrate: A Transmission Electron Microscopy Study. Journal of Nanoscience and Nanotechnology, 2011, 11, 5108-5113.	0.9	10
125	1220-1280-nm Optically Pumped InAs Quantum Dot-Based Vertical External-Cavity Surface-Emitting Laser. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1787-1793.	1.9	10
126	High power 1.25- μ m InAs quantum dot vertical external-cavity surface-emitting laser. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, .	0.6	8

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127	Growth and thermal conductivity analysis of polycrystalline GaAs on chemical vapor deposition diamond for use in thermal management of high-power semiconductor lasers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 03C130.	0.6	7
128	Measuring the transition switching speed of a semiconductor-based photoconductive switch using RF techniques. , 2011, , .		5
129	Effect of dislocation density on thermal boundary conductance across GaSb/GaAs interfaces. Applied Physics Letters, 2011, 98, .	1.5	73
130	Perforated (In)GaSb quantum wells on GaSb substrates through the use of As ₂ based in situ etches. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 041204.	0.6	1
131	TEM Characterization of GaSb Growth on GaAs (001) Substrate: Growth Mode and Defect Evaluation. Microscopy and Microanalysis, 2010, 16, 1516-1517.	0.2	0
132	340-W Peak Power From a GaSb 2- μ m Optically Pumped Semiconductor Laser (OPSL) Grown Mismatched on GaAs. IEEE Photonics Technology Letters, 2010, 22, 1253-1255.	1.3	14
133	Characterization of thin GaAs films grown on nanostructured silicon substrates. , 2010, , .		2
134	Multi-watt 1.25 μ m quantum dot VECSEL. Electronics Letters, 2010, 46, 856.	0.5	18
135	Mid-infrared InAs/GaSb strained layer superlattice detectors with nBn design grown on a GaAs substrate. Semiconductor Science and Technology, 2010, 25, 085010.	1.0	56
136	Optically Pumped Frequency Reconfigurable Antenna Design. IEEE Antennas and Wireless Propagation Letters, 2010, 9, 280-283.	2.4	107
137	Implementation of a cognitive radio front-end using optically reconfigurable antennas. , 2010, , .		13
138	Optically pumped reconfigurable antenna systems (OPRAS). , 2010, , .		9
139	Record pulsed power demonstration of a 2 μ m GaSb-based optically pumped semiconductor laser grown lattice-mismatched on an AlAs/GaAs Bragg mirror and substrate. Applied Physics Letters, 2009, 95, 081112.	1.5	11
140	Interfacial misfit array formation for GaSb growth on GaAs. Journal of Applied Physics, 2009, 105, .	1.1	87
141	Compensation of interfacial states located inside the δ -buffer-free GaSb/GaAs (001) heterojunction via Γ -doping. Applied Physics Letters, 2009, 95, 072109.	1.5	12
142	Influence of background gas atmosphere on formation of Cr ₂ O ₃ thin films prepared by pulsed laser deposition. Surface Engineering, 2009, 25, 223-227.	1.1	12
143	Continuous-Wave, Room-Temperature Operation of 2- μ m Sb-Based Optically-Pumped Vertical-External-Cavity Surface-Emitting Laser Monolithically Grown on GaAs Substrates. Applied Physics Express, 2009, 2, 112102.	1.1	10
144	Monolithically Integrated III-Sb-Based Laser Diodes Grown on Miscut Si Substrates. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 716-723.	1.9	23

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145	Structural Analysis of Highly Relaxed GaSb Grown on GaAs Substrates with Periodic Interfacial Array of 90° Misfit Dislocations. <i>Nanoscale Research Letters</i> , 2009, 4, 1458-62.	3.1	50
146	Coulomb effects in type-II Ga(As)Sb quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , 2009, 246, 752-755.	0.7	21
147	Optical transition pathways in type-II Ga(As)Sb quantum dots. <i>Journal of Luminescence</i> , 2009, 129, 456-460.	1.5	16
148	Formation and Optical Characteristics of Type-II Strain-Relieved GaSb/GaAs Quantum Dots by Using an Interfacial Misfit Growth Mode. <i>IEEE Nanotechnology Magazine</i> , 2009, 8, 269-274.	1.1	7
149	Electronic characteristics of the interfacial states embedded in GaSb/GaAs (001) heterojunctions. <i>Applied Physics Letters</i> , 2009, 95, 202107.	1.5	9
150	Characterization of Interfacial Misfit Array Formation for GaSb Growth on GaAs by Transmission Electron Microscopy. <i>Microscopy and Microanalysis</i> , 2009, 15, 1062-1063.	0.2	3
151	Device Characteristics of GaInSb/AlGaSb Quantum Well Lasers Monolithically Grown on GaAs Substrates by Using an Interfacial Misfit Array. <i>Journal of Electronic Materials</i> , 2008, 37, 1758-1763.	1.0	3
152	Quantum ring formation and antimony segregation in GaSb/GaAs nanostructures. <i>Journal of Vacuum Science & Technology B</i> , 2008, 26, 1492-1503.	1.3	48
153	Time-resolved photoluminescence of type-II Ga(As)Sb/GaAs quantum dots embedded in an InGaAs quantum well. <i>Nanotechnology</i> , 2008, 19, 295704.	1.3	24
154	Fabrication of Self-Aligned Enhancement-Mode $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ MOSFETs With $\text{TaN/HfO}_2/\text{AlN}$ Gate Stack. <i>IEEE Electron Device Letters</i> , 2008, 29, 557-560.	2.2	43
155	Simultaneous interfacial misfit array formation and antiphase domain suppression on miscut silicon substrate. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	61
156	Monolithically integrated III-Sb based laser diodes grown on miscut Si substrates. , 2008, , .		1
157	Fabrication and characterization of metal-oxide-semiconductor GaAs capacitors on $\text{Ge}_x\text{Si}_{1-x}\text{Ge}_x\text{Si}$ substrates with Al_2O_3 gate dielectric. <i>Journal of Vacuum Science & Technology B</i> , 2008, 26, 1182.	1.3	2
158	Self-Organized Formation of GaSb/GaAs Quantum Rings. <i>Physical Review Letters</i> , 2008, 101, 256101.		67
159	Electrical and structural characterization of a single GaSb/InAs/GaSb quantum well grown on GaAs using interface misfit dislocations. <i>Journal of Applied Physics</i> , 2008, 104, .	1.1	3
160	Interfacial misfit dislocation array based growth of III-Sb active regions on GaAs/AlGaAs DBRs for high-power 2 μm VECSELs. <i>Proceedings of SPIE</i> , 2008, , .	0.8	7
161	Monolithically Integrated III-Sb Superluminescent Light Emitting Diodes on Si (100) Substrates. , 2007, , .		0
162	Monolithically integrated III-Sb CW super-luminal light emitting diodes on non-miscut Si (100) substrates. <i>Electronics Letters</i> , 2007, 43, 244.	0.5	6

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163	1.54- μm GaSb/AlGaSb multi-quantum-well monolithic laser at 77 K grown on miscut Si substrate using interfacial misfit arrays. Electronics Letters, 2007, 43, 1198.	0.5	30
164	Room temperature InGaSb quantum well microcylinder lasers at 2- μm grown monolithically on a silicon substrate. Journal of Vacuum Science & Technology B, 2007, 25, 1622.	1.3	9
165	Optical properties of patterned InAs quantum dot ensembles grown on GaAs nanopillars. Applied Physics Letters, 2007, 91, .	1.5	19
166	Single dot spectroscopy of site-controlled InAs quantum dots nucleated on GaAs nanopillars. Applied Physics Letters, 2007, 91, 133104.	1.5	27
167	Room-temperature lasing at 1.82- μm of GaInSb/AlGaSb quantum wells grown on GaAs substrates using an interfacial misfit array. Applied Physics Letters, 2007, 91, 141102.	1.5	23
168	Epitaxial growth and formation of interfacial misfit array for tensile GaAs on GaSb. Applied Physics Letters, 2007, 90, 161902.	1.5	39
169	1.55- μm GaSb/AlGaSb MQW diode lasers grown on GaAs substrates using interfacial misfit (IMF) arrays. , 2007, , .		2
170	Monolithically integrated III-Sb diode lasers on Si using interfacial misfit arrays. , 2007, , .		0
171	Arsenic-induced etched nanovoids on GaSb (100). Journal of Applied Physics, 2007, 102, 044312.	1.1	5
172	Lasing characteristics of GaSb/GaAs self-assembled quantum dots embedded in an InGaAs quantum well. Applied Physics Letters, 2007, 90, 261115.	1.5	54
173	Controlled InAs quantum dot nucleation on faceted nanopatterned pyramids. Applied Physics Letters, 2007, 90, 183103.	1.5	50
174	Type II Strain Layer Superlattices (SLS's) grown on GaAs Substrates. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	0
175	1.65- μm buffer-free GaSb/AlGaSb quantum-well diode lasers grown on a GaAs substrate operating at room temperature. Device Research Conference, IEEE Annual, 2007, , .	0.0	0
176	Room-Temperature Operation of Buffer-Free GaSb/AlGaSb Quantum-Well Diode Lasers Grown on a GaAs Platform Emitting at 1.65 μm . IEEE Photonics Technology Letters, 2007, 19, 1628-1630.	1.3	33
177	Atomistic modeling of strain distribution in self-assembled interfacial misfit dislocation (IMF) arrays in highly mismatched III-V semiconductor materials. Journal of Crystal Growth, 2007, 303, 449-455.	0.7	67
178	III/V ratio based selectivity between strained Stranski-Krastanov and strain-free GaSb quantum dots on GaAs. Applied Physics Letters, 2006, 89, 161104.	1.5	89
179	Room-Temperature Optically Pumped (Al)GaSb Vertical-Cavity Surface-Emitting Laser Monolithically Grown on an Si(1 0 0) Substrate. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1636-1641.	1.9	41
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